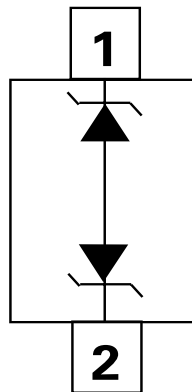


SD-C Series 450W Discrete Bidirectional TVS Diode



Pinout and Functional Block Diagram



Description

The SD-C series can safely absorb repetitive ESD strikes at $\pm 30\text{kV}$ (contact discharge, IEC 61000-4-2) without performance degradation and safely dissipate 30A (SD05C) of 8/20 μs induced surge current (IEC 61000-4-5 2nd Edition) with very low clamping voltages.

Features

- ESD, IEC 61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd Edition, 30A ($t_p=8/20\mu\text{s}$, SD05C)
- Low clamping voltage
- Low leakage current
- Small SOD323 package fits 0805 footprints
- AEC-Q101 qualified
- RoHS Compliant and Lead Free
- Moisture Sensitivity Level (MSL-1)

Applications

- Switches / Buttons
- Test Equipment / Instrumentation
- Point-of-Sale Terminals
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- Automotive Electronics

Additional Information



Datasheet



Resources



Samples

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{pk}	Peak Pulse Power ($t_p=8/20\mu s$)	450	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Thermal Information

Parameter	Rating	Units
Storage Temperature Range	-55 to 150	°C
Maximum Junction Temperature	150	°C
Maximum Lead Temperature (Soldering 20-40s)	260	°C

SD05C Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			5.0	V
Reverse Voltage Drop	V_R	$I_R = 1mA$	6.0			V
Leakage Current	I_{LEAK}	$V_R = 5V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP} = 1A, t_p = 8/20\mu s, Fwd$			10.0	V
		$I_{PP} = 10A, t_p = 8/20\mu s, Fwd$			14.5	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p = 100ns$, I/O to Ground		0.31		Ω
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu s$			30.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	C_D	Reverse Bias=0V, f=1MHz			200	pF

SD12C Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			12.0	V
Reverse Voltage Drop	V_R	$I_R = 1mA$	13.3			V
Leakage Current	I_{LEAK}	$V_R = 12V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP} = 1A, t_p = 8/20\mu s, Fwd$			18.5	V
		$I_{PP} = 10A, t_p = 8/20\mu s, Fwd$			23.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p = 100ns$, I/O to Ground		0.41		Ω
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu s$			17.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	C_{D-GND}	Reverse Bias=0V, f=1MHz			100	pF

SD15C Electrical Characteristics (T_{Op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			15.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	16.7			V
Leakage Current	I _{LEAK}	V _R = 15V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20 μs, Fwd			24.0	V
		I _{PP} = 10A, t _p = 8/20 μs, Fwd			31.0	V
Dynamic Resistance ²	R _{DYN}	TLP, tp = 100ns, I/O to Ground		0.46		Ω
Peak Pulse Current	I _{PP}	t _p = 8/20 μs			12.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias = 0V, f = 1MHz			75	pF

SD24C Electrical Characteristics (T_{Op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			24.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	26.7			V
Leakage Current	I _{LEAK}	V _R = 24V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20 μs, Fwd			34.0	V
		I _{PP} = 5A, t _p = 8/20 μs, Fwd			42.0	V
Dynamic Resistance ²	R _{DYN}	TLP, tp = 100ns, I/O to Ground		0.62		Ω
Peak Pulse Current	I _{PP}	t _p = 8/20 μs			7.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias = 0V, f = 1MHz			50	pF

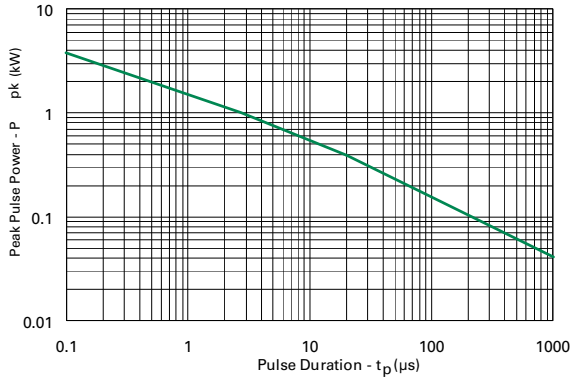
SD36C Electrical Characteristics (T_{Op}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			36.0	V
Reverse Voltage Drop	V _R	I _R = 1 mA	40.0			V
Leakage Current	I _{LEAK}	V _R = 36V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1A, t _p = 8/20 μs, Fwd			50.0	V
		I _{PP} = 4A, t _p = 8/20 μs, Fwd			60.0	V
Dynamic Resistance ²	R _{DYN}	TLP, tp = 100ns, I/O to Ground		0.68		Ω
Peak Pulse Current	I _{PP}	t _p = 8/20 μs			5.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±30			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias = 0V, f = 1MHz			30	pF

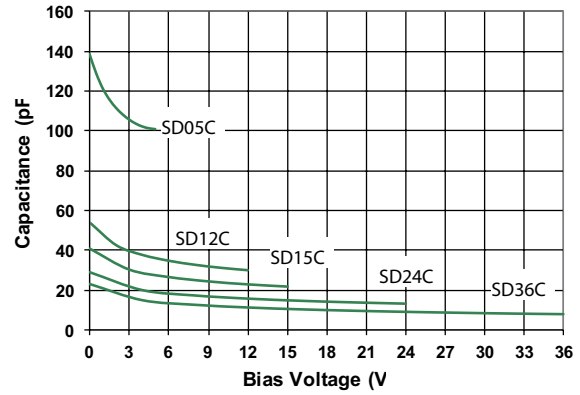
Note:

- Parameter is guaranteed by design and/or device characterization.
- Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

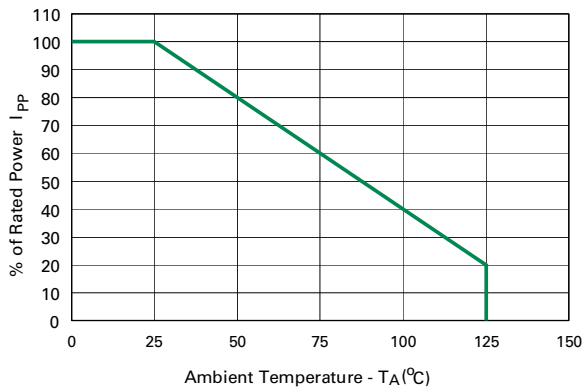
Non-Repetitive Peak Pulse Power vs. Pulse Time



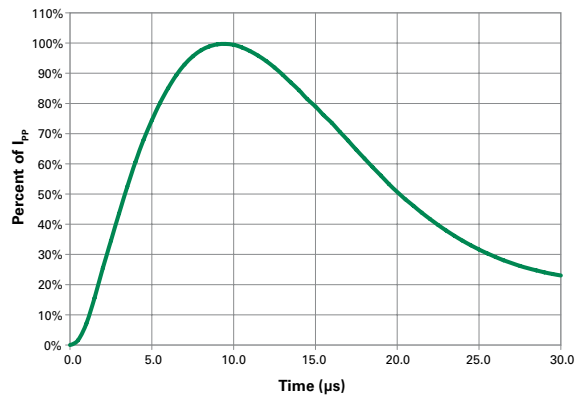
Capacitance vs. Bias



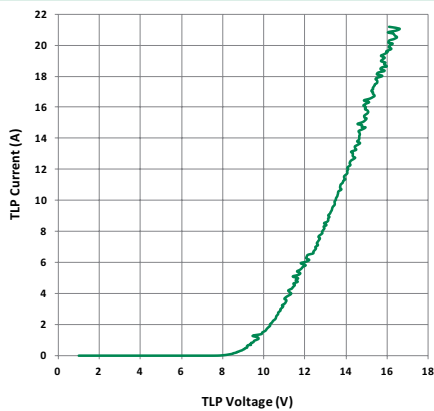
Power Derating Curve



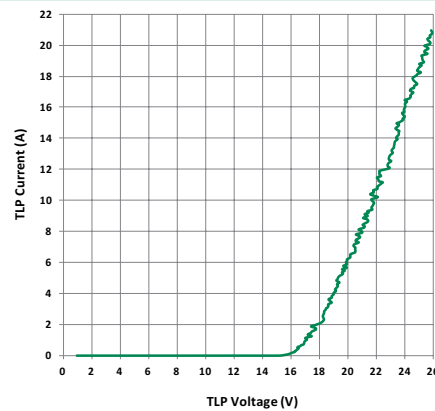
8/20 μ s Pulse Waveform



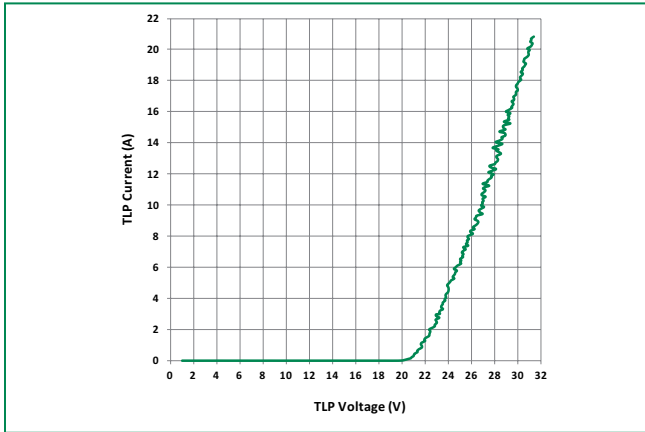
SD05C Transmission Line Pulsing (TLP) Plot



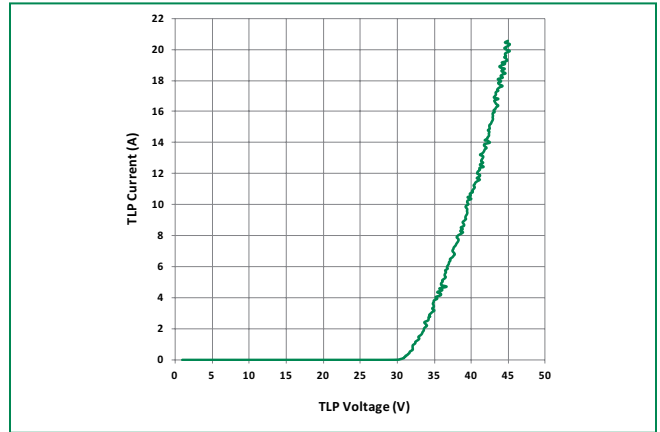
SD12C Transmission Line Pulsing (TLP) Plot



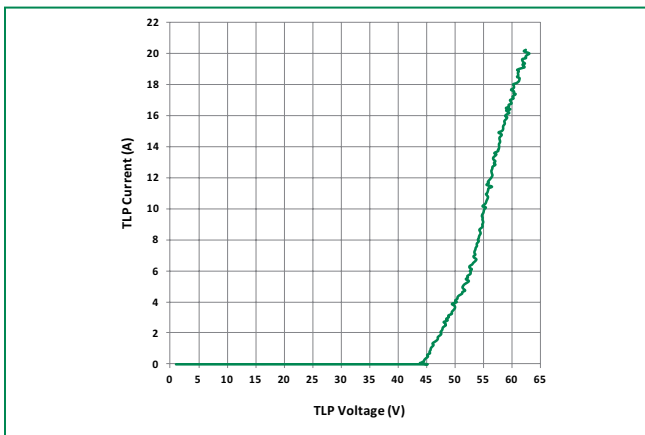
SD15C Transmission Line Pulsing(TLP) Plot



SD24C Transmission Line Pulsing(TLP) Plot

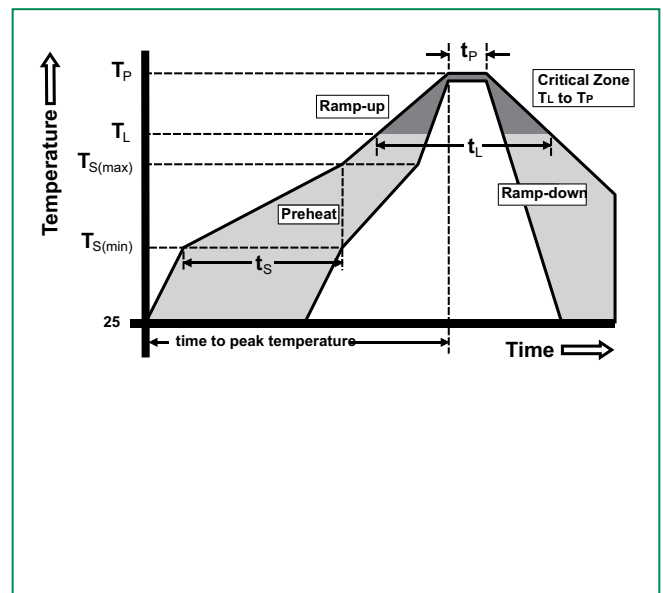


SD36C Transmission Line Pulsing(TLP) Plot



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Product Characteristics

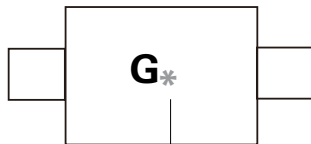
Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substrate material	Silicon
Body Material	V-0 per UL 94 Molded Epoxy

- Notes :
1. All dimensions are in millimeters
 2. Dimensions include solder plating.
 3. Dimensions are exclusive of mold flash & metal burr.
 4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
 5. Package surface matte finish VDI 11-13.

Ordering Information

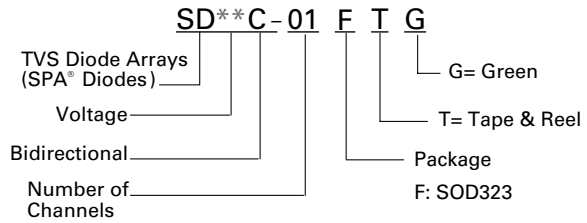
Part Number	Package	Marking	Min. Order Qty.
SD05C-01FTG	SOD323	G	3000
SD12C-01FTG	SOD323	G1	3000
SD15C-01FTG	SOD323	G2	3000
SD24C-01FTG	SOD323	G3	3000
SD36C-01FTG	SOD323	G4	3000

Part Marking System

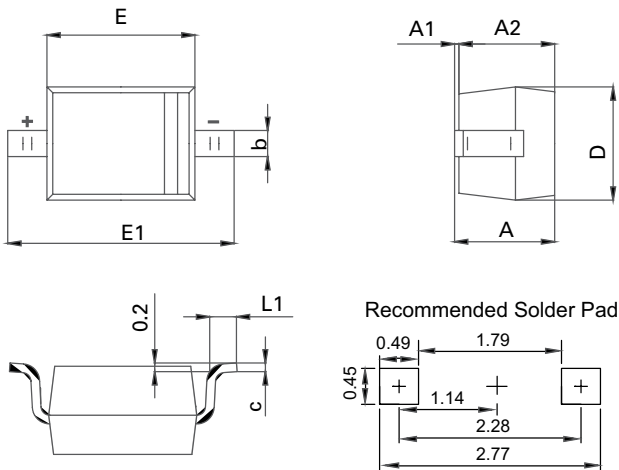


- Blank: SD05C-01FTG
 1: SD12C-01FTG
 2: SD15C-01FTG
 3: SD24C-01FTG
 4: SD36C-01FTG

Part Numbering System



Package Dimensions -SOD323



Unit: mm

Symbol	SOD323			
	Millimeters		Inches	
	Min	Max	Min	Max
A	0.8	1.14	0.031	0.045
A1	0.00	0.10	0.000	0.004
A2	0.80	1.04	0.031	0.014
b	0.25	0.35	0.010	0.014
c	0.08	0.15	0.003	0.006
D	1.15	1.45	0.045	0.057
E	1.60	1.90	0.063	0.075
E1	2.44	2.70	0.096	0.106
L1	0.25	0.45	0.010	0.018

Embossed Carrier Tape & Reel Specification – SOD323

